Supplementary Information

Table S1. Device characteristics presented in the order of appearance in the text.

Sample	**Backing layer**					**ZnO rods**	**Active Layer**		**Device Characteristics**			
	ZnO Dip-coating	ZnO Spin-coating	ZnO s.-p. MeOH	ZnO s.-p. DMF	TiO_2 s.-p.	Method	Z907^{dip}	Polymer	J_{sc} (mAcm^{-2})	V_{oc} (V)	FF (%)	η (%)
1	✓					---		P3HT^{spin}	---	---	---	---
2		✓				---		P3HT^{spin}	---	---	---	---
3			✓			---		P3HT^{spin}	0.21	0.21	45.2	0.028
4				✓		---		P3HT^{spin}	0.12	0.12	35.3	0.005
5					✓	---		P3HT^{spin}	0.12	0.36	45.5	0.019
6	✓					1,2,3		P3HT$^{dip+spin}$	---	---	---	---
7			✓			1,3		P3HT$^{dip+spin}$	---	---	---	---
8					✓	2 (6h)		P3HT$^{dip+spin}$	0.20	0.06	28.0	0.003
9			✓			2 (6h)		P3HT$^{dip+spin}$	1.33	0.15	30.9	0.06
10			✓			2 (12h)		P3HT$^{dip+spin}$	1.37	0.14	31.9	0.06
11			✓			2 (24h)		P3HT$^{dip+spin}$	0.87	0.11	28.6	0.03
12			✓			2 (6h)	✓	P3HT$^{dip+spin}$	1.73	0.30	38.9	0.20
13			✓			2 (6h)	✓	TPD(4M)-MEH-M3EH-PPV$^{dip+spin}$	1.52	0.29	34.3	0.15